

## INDIAN INSTITUTE OF TECHNOLOGY BOMBAY MATERIALS MANAGEMENT DIVISION Powai, Mumbai 400076.

(PR No. 1000040082)

(Rfx No. 6100001759)

## Technical Specifications for AMC for Transmission Electron Microscopy 300 KV (Qty: 1 Nos.)

| Sr.<br>No | Specification   | Compliance<br>(Yes/No) | Additional<br>Information<br>if any |
|-----------|---|------------------------|-------------------------------------|
| 1.        | Configuration   |                        |                                     |
|           | 1. Extreme Field Emission Gun ( X-FEG):   |                        |                                     |
|           | <ol> <li>Brightness (≥ 7*107 A/m2 sr V)</li> <li>Current (≥ 50nA before Monochromator)</li> <li>Current Stability (≤ 1% over 7 days</li> <li>Spatial Coherency</li> <li>Temporal Coherency (Energy Resolution at 300KV</li> <li>without Monochromator ≤ 0.8eV)</li> </ol> |                        |                                     |
|           | 2. Accelerator:   |                        |                                     |
|           | 1. 60 to 300 KV   |                        |                                     |
|           | 3. 3 Lens Condenser   |                        |                                     |
|           | <ol> <li>Large parallel illumination range in TEM (nm to µm range)</li> <li>Large convergence angle range in STEM</li> </ol>  |                        |                                     |
|           | 4. Super-Twin Objective Lens  |                        |                                     |
|           | <ol> <li>Wide Pole Piece Gap (5mm)</li> <li>Large sample tilting range (±70)</li> </ol>   |                        |                                     |
|           | 5. Piezo Stage  |                        |                                     |
|           | 1. Atomic step size (20pm) in X, Y and Z  |                        |                                     |

| 6             | . Super-X EDS Detectors  |
|---------------|--|
|               | 1. 4 Silicon Drift Detectors / Windowless 2. Large Solid Angle (0.9 srad) 3. High Throughput rate (>240kcps) 4. Dwell Times per Pixel < 10µs  1. 4K*4K CMOS Camera   |
| 2. <b>Spe</b> | ecification of the instrument:   |
|               | 1. Point resolution <= 0.20 nm 2. Information Limit <= 0.1 nm 3. Maximum specimen Drift <= 0.5 nm/min 4. Minimum Reduced Brightness 7.5 x 107 A/ (m2·sr·V) 5. Probe Current 1 nm spot a. Probe size ≤ 0.2 nm b. Specification current: ≥ 0.25 nA 6. Maximum Spot Drift <=0.5 nm/min 7. Maximum Resolution HAADF £ 0.136 nm (STEM RESOLUTION) 8. EDS energy resolution at Mn ≤ 136 eV (all detectors) 9. EDS energy resolution at Mn ≤ 140 eV (all detectors) (At 100 Kcps) |
| 3. <b>Scc</b> | pe of work   |
| 1.            | PM & Unlimited Break Down Visit  1st PM will be standard and for 2nd PM call has to be registered by User department.  All the third-party items are excluded from the scope of work   |
| 4. Ser        | vice Level Agreement   |
|               | PM & Unlimited Break Down Visit  |
| 1.            | Emergency visits will be unlimited. Replacement parts will be at customer's cost.  |